

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	62	Kelvin adj effect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/10 12:58
L4	448	438/428.ccls. 438/436.ccls. 438/674.ccls.	US-PGPUB; USPAT	OR	OFF	2006/02/10 13:06
L5	6124	438/428.ccls. 438/436.ccls. 438/674.ccls. 438/681.ccls. 438/685.ccls. 438/687.ccls. 438/688.ccls. 438/763.ccls. 438/778.ccls. 438/782.ccls. 438/790.ccls.	US-PGPUB; USPAT	OR	OFF	2006/02/10 13:29
L6	212	L5 and ((gap trench groove inlaid damascene "in-laid" slot recess concav\$6) same liqui\$10 same (precursor solid vapor condens\$8 fill\$6))	US-PGPUB; USPAT	OR	ON	2006/02/10 13:29
L8	128	(substrate semiconductor wafer silicon) same ((gap trench groove inlaid damascene "in-laid" slot recess concav\$6) with liqui\$10 with (precursor solid vapor condens\$8) with (selectiv\$6 fill\$6))	US-PGPUB; USPAT	OR	ON	2006/02/10 14:06
L9	233	(substrate semiconductor wafer silicon) and (gap trench groove inlaid damascene "in-laid" slot recess concav\$6) and liqui\$10 and (precursor solid vapor condens\$8) and (selectiv\$6 fill\$6)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/10 14:05
L10	0	(Kelvin adj effect).clm.	US-PGPUB	OR	ON	2006/02/10 14:06
L11	327	((substrate semiconductor wafer silicon) and (gap trench groove inlaid damascene "in-laid" slot recess concav\$6) and liqui\$10 and (precursor solid vapor condens\$8) and (selectiv\$6 fill\$6)).clm.	US-PGPUB	OR	ON	2006/02/10 14:09
L12	133	((substrate semiconductor wafer silicon) and (gap trench groove inlaid damascene "in-laid" slot recess concav\$6) and liqui\$10 and (precursor solid) and (vapor condens\$8) and (selectiv\$6 fill\$6)).clm.	US-PGPUB	OR	ON	2006/02/10 14:09